

V_{DSS}	600V
$R_{DS(on)}(Max.)$	0.62Ω
I_D	±7A
P_D	78W

●Features

- 1) Low on-resistance.
- 2) Ultra fast switching speed.
- 3) Parallel use is easy.
- 4) Pb-free lead plating ; RoHS compliant

●Application

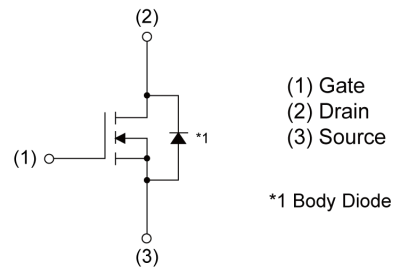
Switching

●Outline

TO-263
SC-83
LPT(S)



●Inner circuit



●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	330
Tape width (mm)	24	
Basic ordering unit (pcs)	1000	
Taping code	TL	
Marking	R6007KNJ	

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	600	V
Continuous drain current ($T_c = 25^\circ\text{C}$)	I_D^{*1}	±7	A
Pulsed drain current	I_{DP}^{*2}	±21	A
Gate - Source voltage	static	±20	V
	AC($f > 1\text{Hz}$)	±30	V
Avalanche current, single pulse	I_{AS}	1.3	A
Avalanche energy, single pulse	E_{AS}^{*3}	133	mJ
Power dissipation ($T_c = 25^\circ\text{C}$)	P_D	78	W
Junction temperature	T_j	150	°C
Operating junction and storage temperature range	T_{stg}	-55 to +150	°C

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}^{*4}	-	-	1.6	°C/W
Thermal resistance, junction - ambient	R_{thJA}^{*5}	-	-	80	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	600	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$	-	-	100	μA
		$T_j = 125^\circ\text{C}$	-	-	1000	
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	3	-	5	V
Static drain - source on - state resistance	$R_{DS(on)}^{*6}$	$V_{GS} = 10V, I_D = 2.4A$	-	0.57	0.62	Ω
		$T_j = 125^\circ\text{C}$	-	1.20	-	
Gate resistance	R_G	$f = 1MHz, \text{open drain}$	-	3.2	-	Ω

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Forward Transfer Admittance	$ Y_{fs} ^{*6}$	V _{DS} = 10V, I _D = 3.5A	1.9	3.8	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	470	-	pF
Output capacitance	C _{oss}	V _{DS} = 25V	-	440	-	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	20	-	
Turn - on delay time	t _{d(on)} ^{*6}	V _{DD} ≈ 300V, V _{GS} = 10V	-	18	-	ns
Rise time	t _r ^{*6}	I _D = 3.5A	-	22	-	
Turn - off delay time	t _{d(off)} ^{*6}	R _L ≈ 86.6Ω	-	35	-	
Fall time	t _f ^{*6}	R _G = 10Ω	-	25	-	

●Gate charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q _g ^{*6}	V _{DD} ≈ 300V	-	14.5	-	nC
Gate - Source charge	Q _{gs} ^{*6}	I _D = 7A	-	4.2	-	
Gate - Drain charge	Q _{gd} ^{*6}	V _{GS} = 10V	-	5.8	-	
Gate plateau voltage	V _(plateau)	V _{DD} ≈ 300V, I _D = 7A	-	6.8	-	V

*1 Limited only by maximum channel temperature allowed.

*2 Pw ≤ 10μs, Duty cycle ≤ 1%

*3 L ≐ 100mH, V_{DD}=50V, R_G=25Ω, STARTING T_j=25°C

*4 T_C=25°C

*5 Mounted on a epoxy PCB FR4 (25mm x 27mm x 0.8mm)

*6 Pulsed

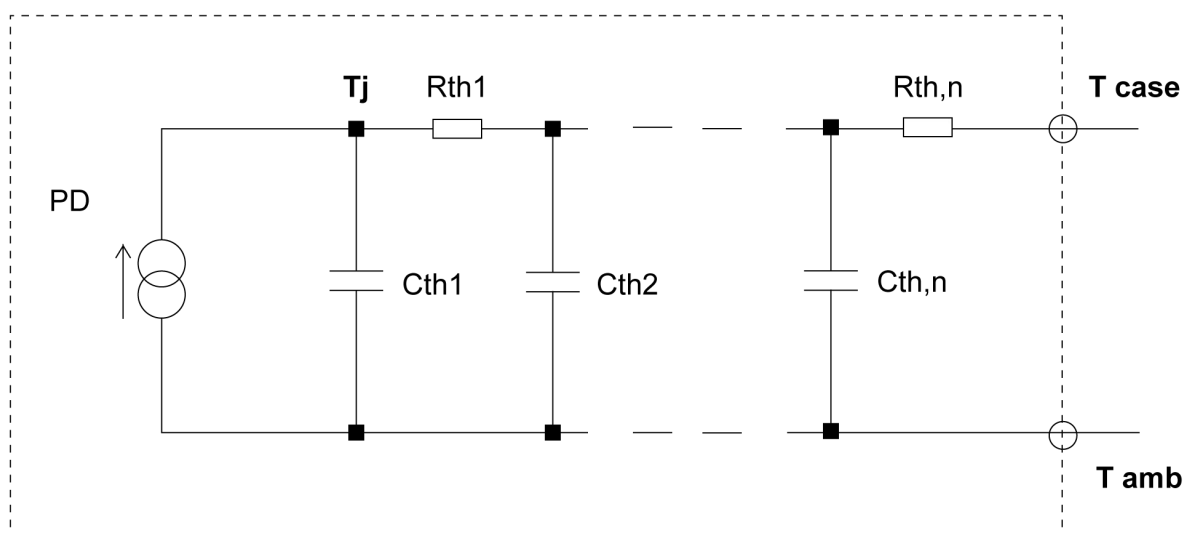
●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous forward current	I_S^{*1}	$T_C = 25^\circ\text{C}$	-	-	7	A
Pulse forward current	I_{SP}^{*2}		-	-	21	A
Forward voltage	V_{SD}^{*6}	$V_{GS} = 0\text{V}, I_S = 7.0\text{A}$	-	-	1.5	V
Reverse recovery time	t_{rr}^{*6}	$I_S = 7\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	302	-	ns
Reverse recovery charge	Q_{rr}^{*6}		-	2.8	-	μC
Peak reverse recovery current	I_{rm}^{*6}		-	18	-	A

●Typical transient thermal characteristics

Symbol	Value	Unit
R_{th1}	0.172	K/W
R_{th2}	0.694	
R_{th3}	0.640	

Symbol	Value	Unit
C_{th1}	0.00102	Ws/K
C_{th2}	0.00288	
C_{th3}	0.153	



● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

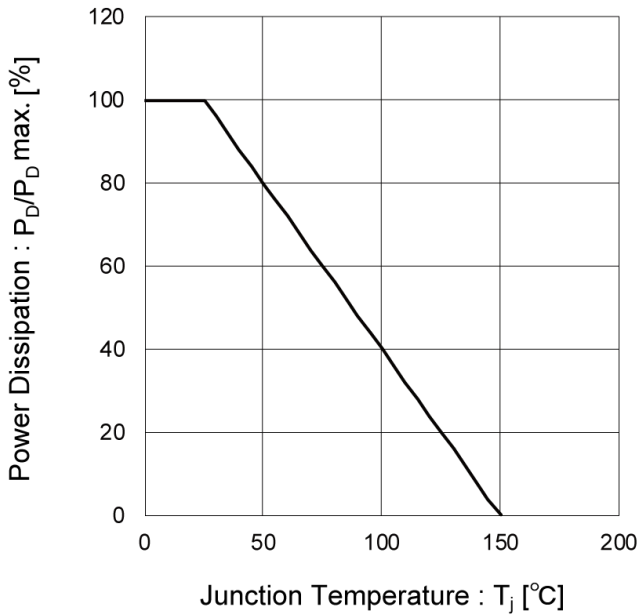


Fig.2 Maximum Safe Operating Area

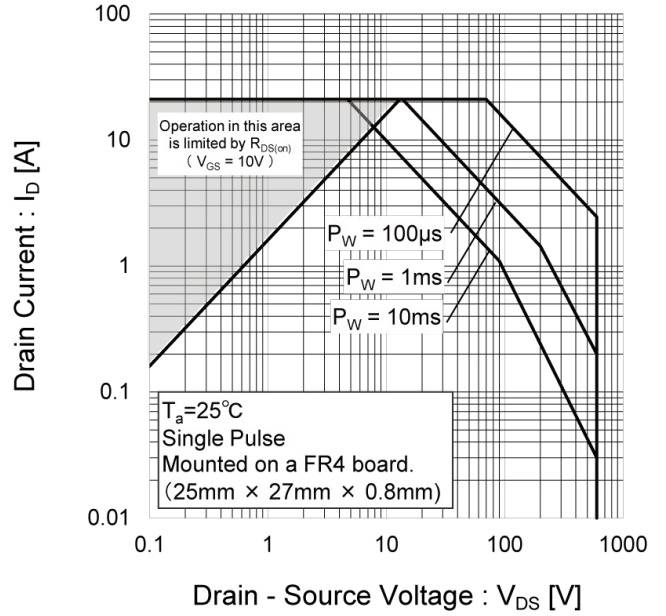
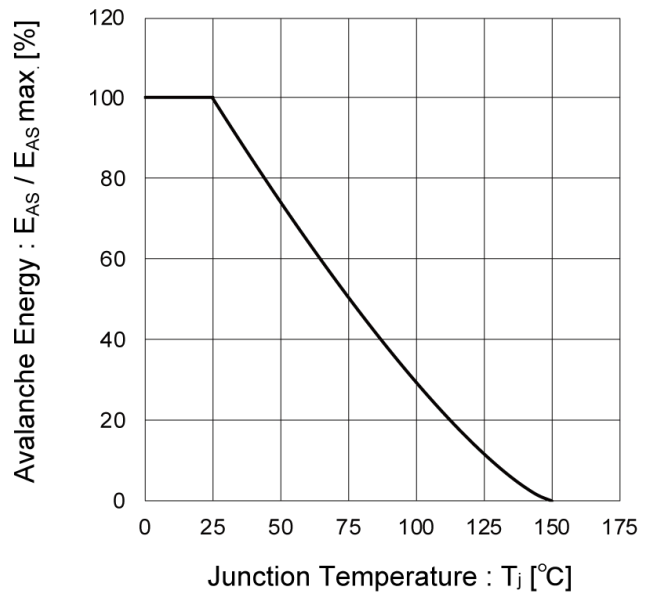


Fig.3 Avalanche Energy Derating Curve vs. Junction Temperature



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

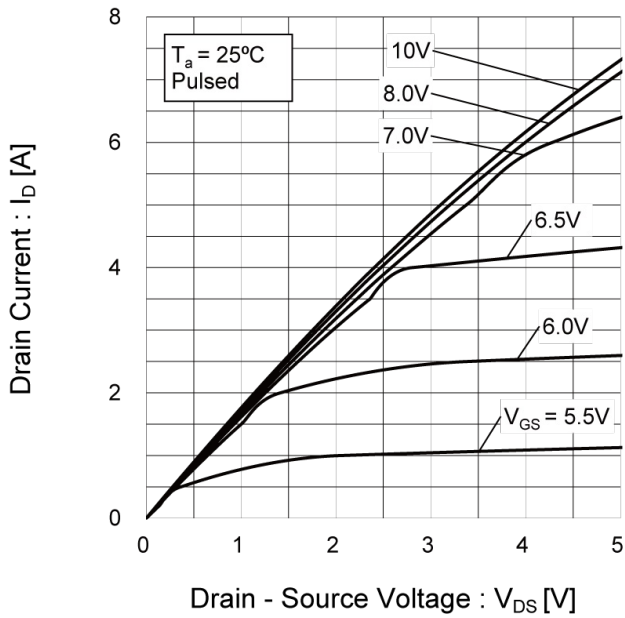
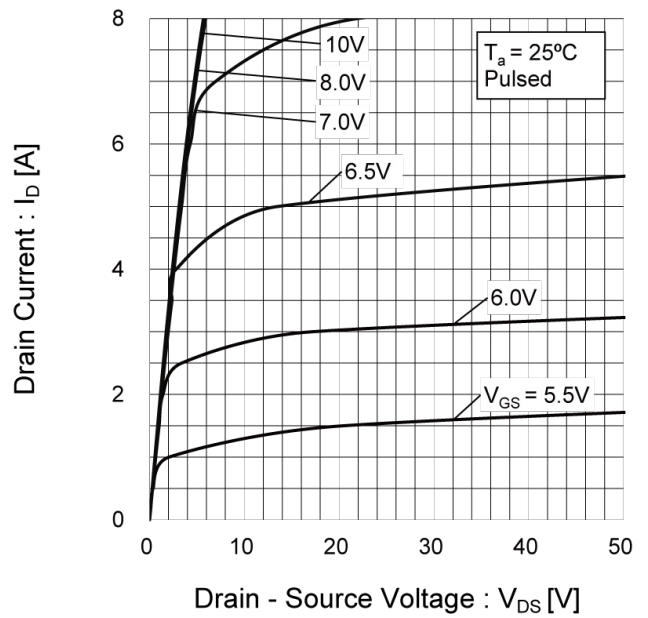


Fig.5 Typical Output Characteristics(II)



● Electrical characteristic curves

Fig.6 Breakdown Voltage vs. Junction Temperature

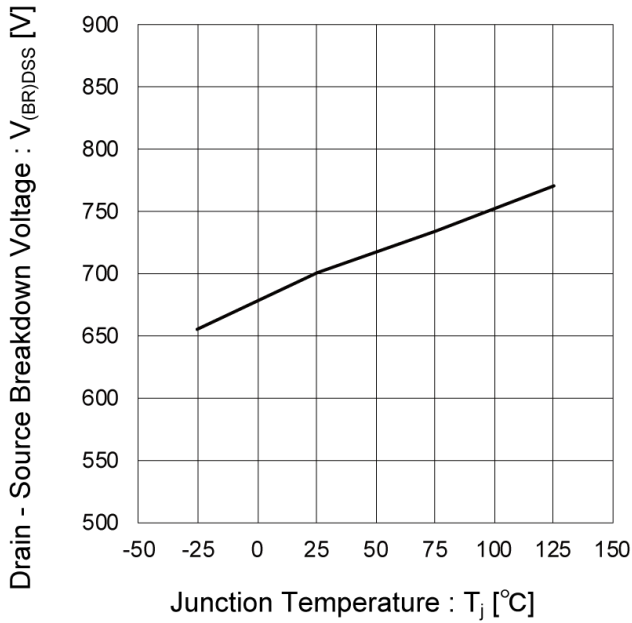


Fig.7 Typical Transfer Characteristics

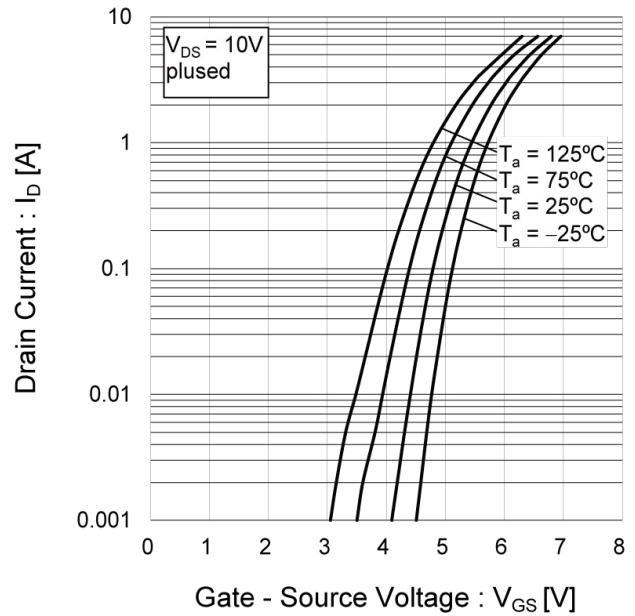


Fig.8 Gate Threshold Voltage vs. Junction Temperature

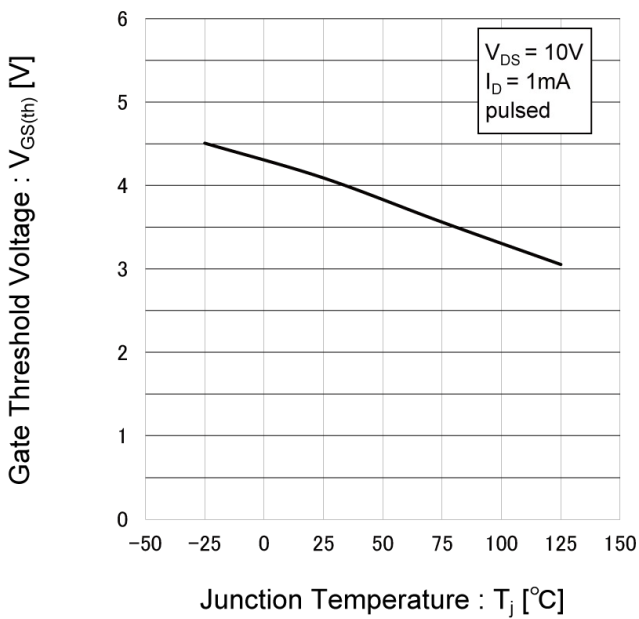
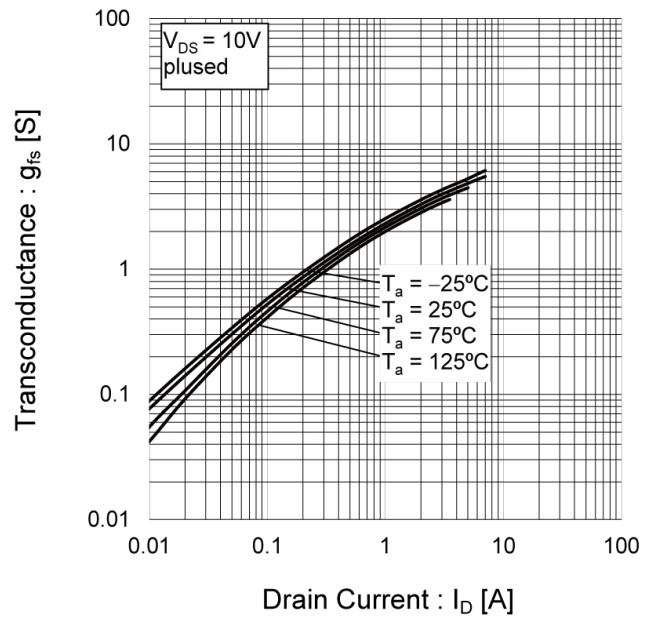


Fig.9 Forward Transfer Admittance vs. Drain Current



● Electrical characteristic curves

Fig.10 Static Drain - Source On - State Resistance vs. Gate Source Voltage

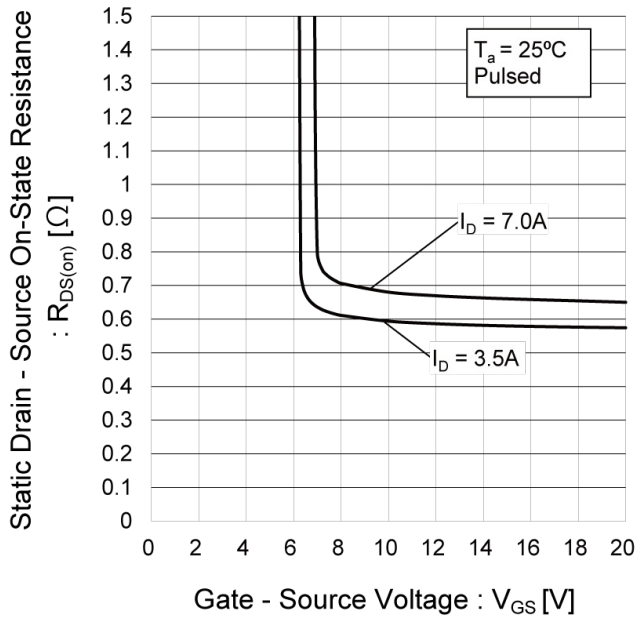


Fig.11 Static Drain - Source On - State Resistance vs. Junction Temperature

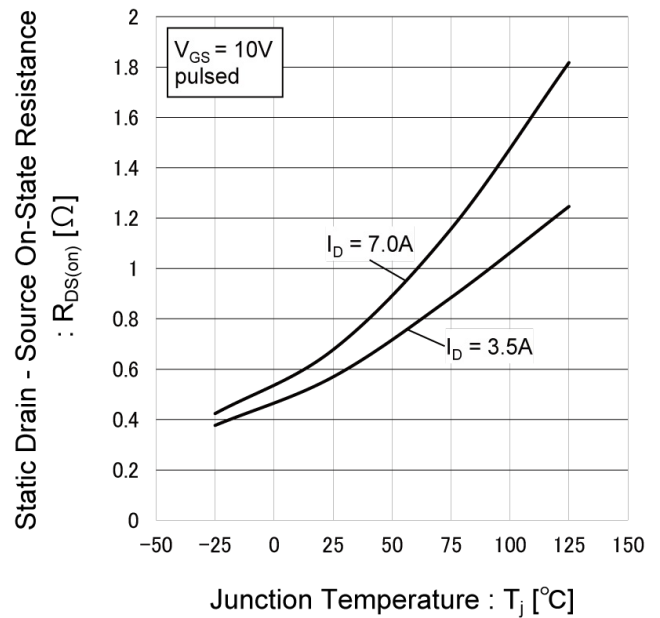
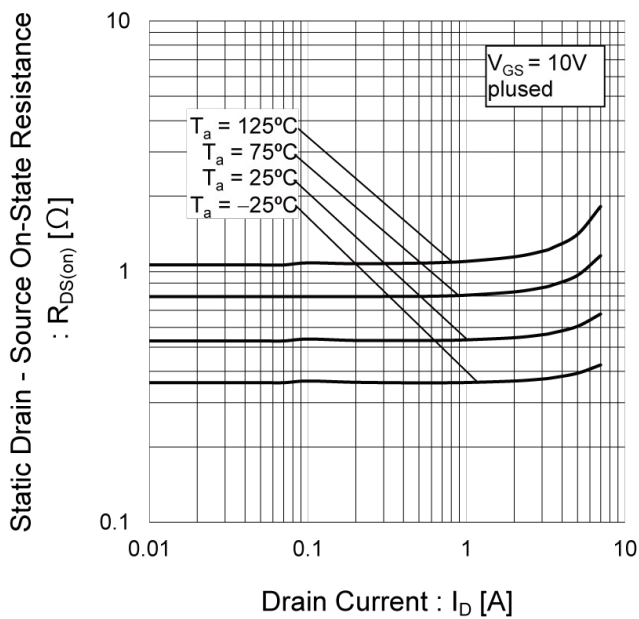


Fig.12 Static Drain - Source On - State Resistance vs. Drain Current(I)



● Electrical characteristic curves

Fig.13 Typical Capacitance vs. Drain - Source Voltage

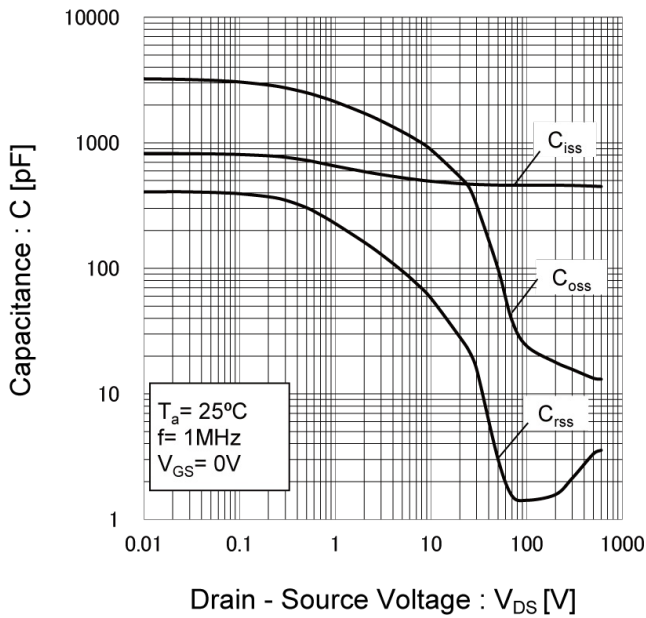


Fig.14 Switching Characteristics

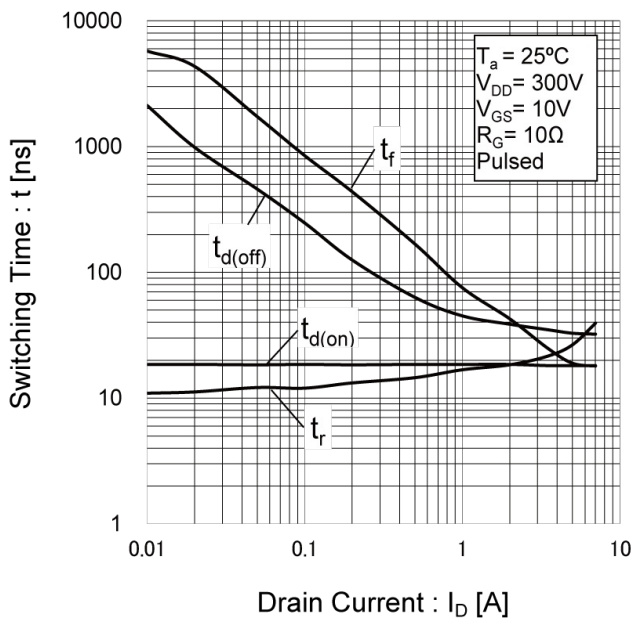
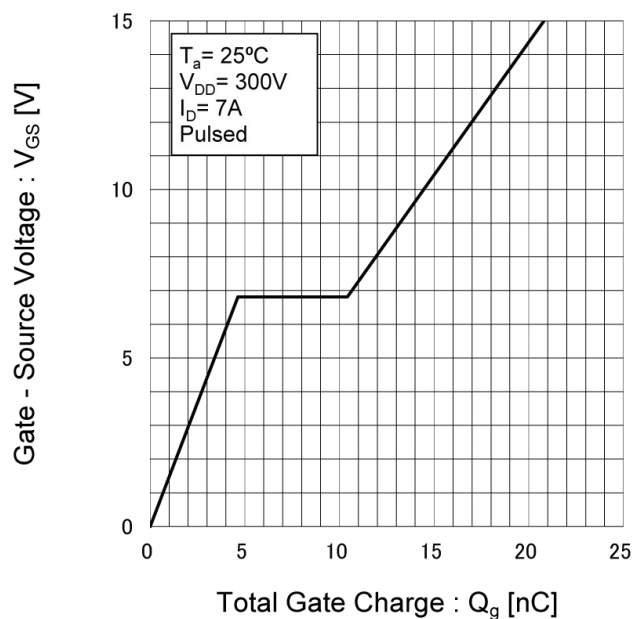


Fig.15 Dynamic Input Characteristics



● Electrical characteristic curves

Fig.16 Inverse Diode Forward Current vs. Source - Drain Voltage

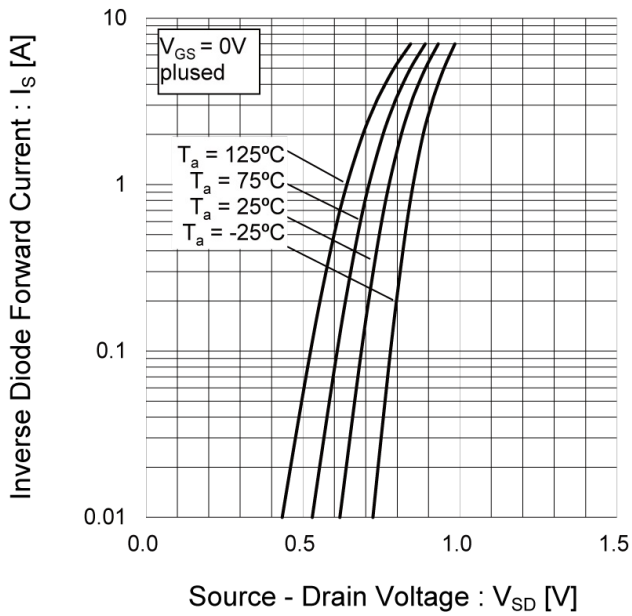
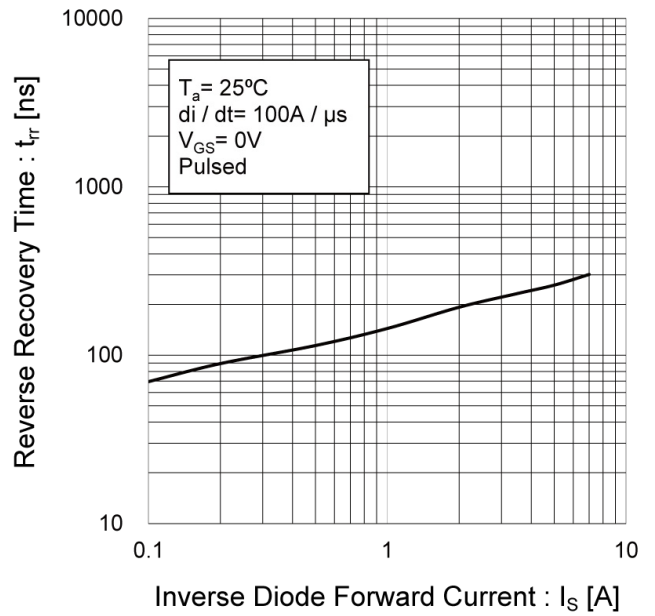


Fig.17 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit



Fig.1-2 Switching Waveforms

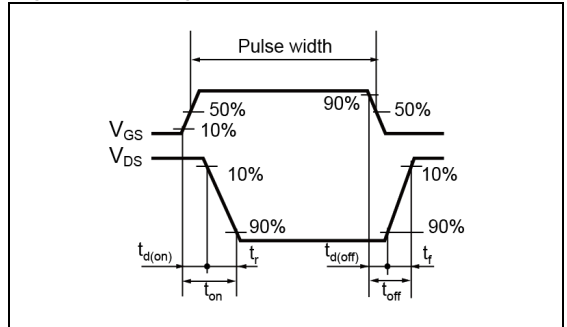


Fig.2-1 Gate Charge Measurement Circuit



Fig.2-2 Gate Charge Waveform

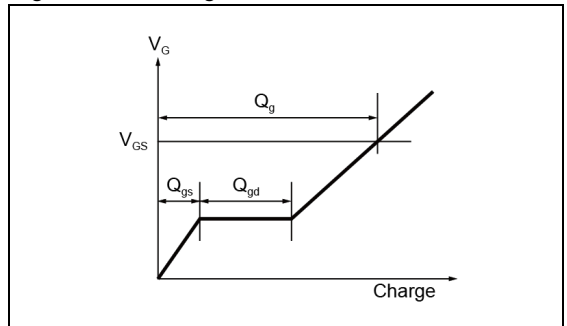


Fig.3-1 Avalanche Measurement Circuit



Fig.3-2 Avalanche Waveform

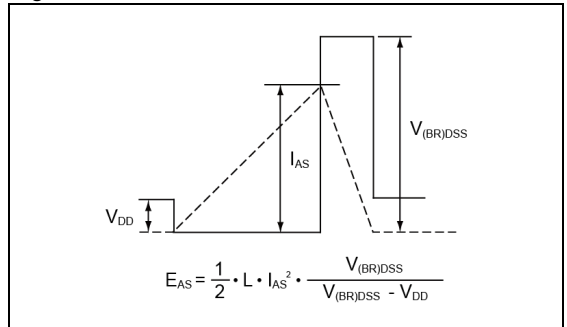


Fig.4-1 dv/dt Measurement Circuit

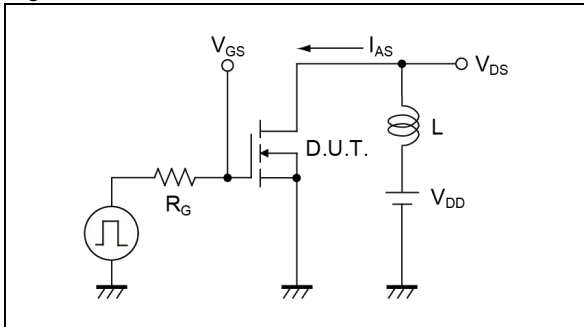


Fig.4-2 dv/dt Waveform

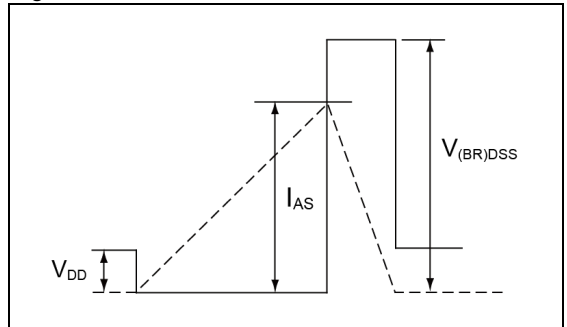


Fig.5-1 dv/dt Measurement Circuit

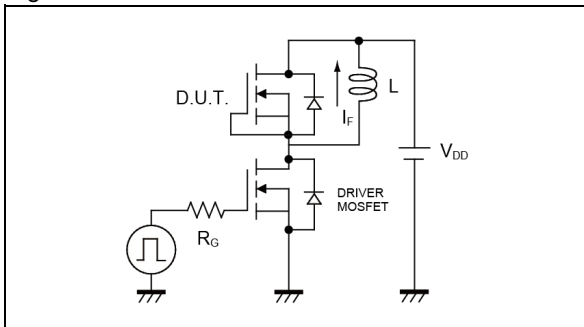
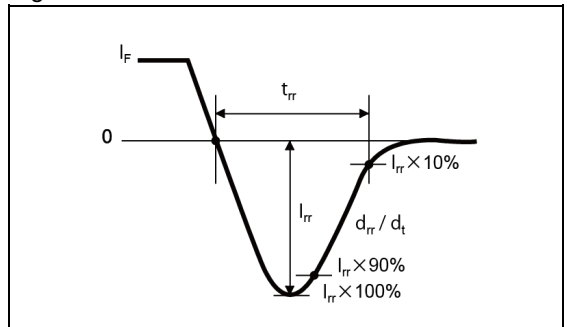
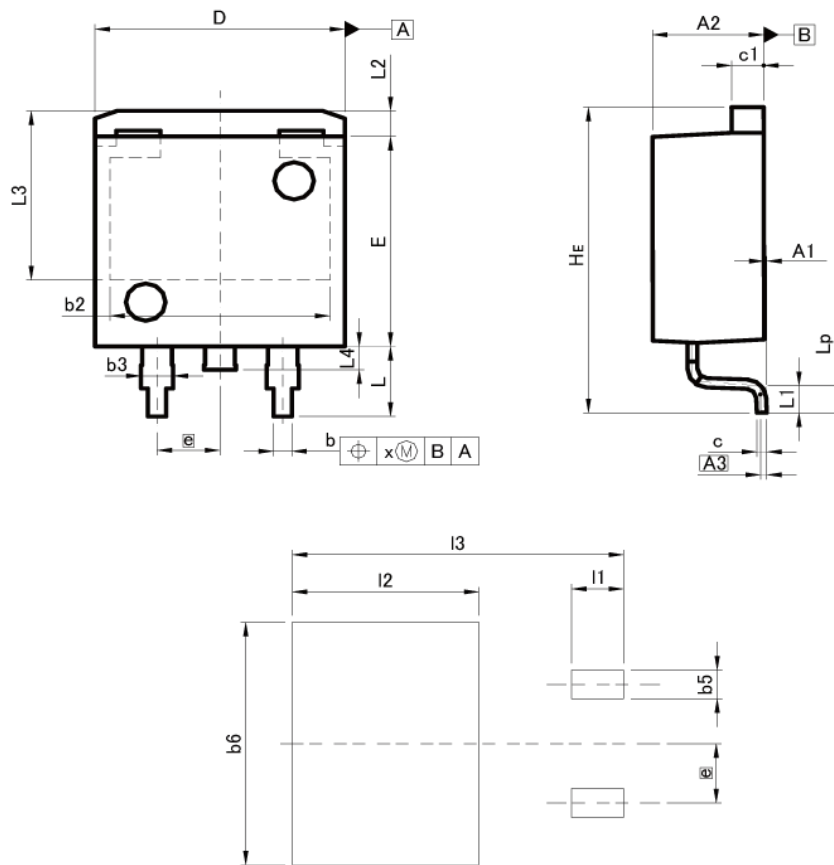


Fig.5-2 dv/dt Waveform



●Dimensions

LPTS
< TO-263 >
(D2PAK)



Pattern of terminal position areas
[Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A1	0.00	0.30	0.000	0.012
A2	4.30	4.70	0.169	0.185
A3	0.25		0.010	
b	0.68	0.98	0.027	0.039
b2	8.90		0.350	
b3	1.14	1.44	0.045	0.057
c	0.30	0.60	0.012	0.024
c1	1.10	1.50	0.043	0.059
D	9.80	10.40	0.386	0.409
E	8.80	9.20	0.346	0.362
e	2.54		0.100	
HE	12.80	13.40	0.504	0.528
L	2.70	3.30	0.106	0.130
L1	0.90	1.50	0.035	0.059
L2	1.10		0.043	
L3	7.25		0.285	
L4	1.00		0.039	
Lp	0.90	1.50	0.035	0.059
x	-	0.25	-	0.010

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b5	-	1.23	-	0.049
b6	-	10.40	-	0.409
l1	-	2.10	-	0.083
l2	-	7.55	-	0.297
l3	-	13.40	-	0.528

Dimension in mm/inches

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